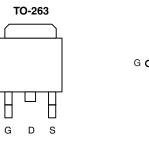
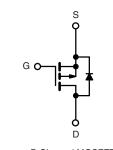


Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	- 60			
$R_{DS(on)}(\Omega)$ at V_{GS} = - 10 V	0.0089			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.0132			
I _D (A)	- 110			
Configuration	Single			





Top View

P-Channel MOSFET

FEATURES

- TrenchFET[®] Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_q and UIS Tested
- AEC-Q101 Qualified^d
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ORDERING INFORMATION			
Package	TO-263		
Lead (Pb)-free and Halogen-free	SQM110P06-8m9L-GE3		

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 60	N	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C	- I _D -	- 110		
Continuous Drain Current	T _C = 125 °C		- 65		
Continuous Source Current (Diode Conduction) ^a		I _S	- 120	A	
Pulsed Drain Current ^b		I _{DM}	- 230		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 65		
Single Pulse Avalanche Energy		E _{AS}	211	mJ	
Movimum Douver Dissignation	T _C = 25 °C	PD	230	W	
Maximum Power Dissipation ^b	T _C = 125 °C	۲D	76	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W
Junction-to-Case (Drain)		R _{thJC}	0.65	0/10

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

1

SQM110P06-8m9L



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	•							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$		- 60	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$		- 2.0	- 2.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = - 60 V	-	-	- 1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = - 60 V, T_J = 125 °C	I	-	- 50	μA	
		$V_{GS} = 0 V$	V_{DS} = - 60 V, T_{J} = 175 °C	-	-	- 250		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = -10 V$	$V_{DS} \le$ - 5 V	- 100	-	-	Α	
		$V_{GS} = -10 V$	I _D = - 30 A	-	0.0071	0.0089	Ω	
Drain-Source On-State Resistance ^a	Б	$V_{GS} = -10 V$	$I_D = -30 \text{ A}, \text{ T}_J = 125 ^\circ\text{C}$	-	-	0.0147		
Drain-Source On-State Resistance	R _{DS(on)}	$V_{GS} = -10 V$	I _D = - 30 A, T _J = 175 °C	-	-	0.0189		
	V _{GS} = - 4.5 V		I _D = - 20 A	-	0.0105	0.0132		
Forward Transconductanceb	9 _{fs}	V _{DS} =	V _{DS} = - 15 V, I _D = - 30 A		71	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		V _{DS} = - 25 V, f = 1 MHz	-	5953	7450	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	750	940		
Reverse Transfer Capacitance	C _{rss}				583	730		
Total Gate Charge ^c	Qg		V _{GS} = - 10 V V _{DS} = - 30 V, I _D = - 110 A		130	200		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V			25	-	nC	
Gate-Drain Charge ^c	Q _{gd}				33	-		
Gate Resistance	Rg	f = 1 MHz		1.2	2.6	4	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	15	25		
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = \text{-} \; 30 \; \text{V}, \; R_{\text{L}} = 0.27 \; \Omega \\ I_{\text{D}} \cong \text{-} \; 110 \; \text{A}, \; V_{\text{GEN}} = \text{-} \; 10 \; \text{V}, \; R_{\text{g}} = 1 \; \Omega \end{array}$		-	15	25	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	71	110		
Fall Time ^c	t _f			-	48	75		
Source-Drain Diode Ratings and Char	acteristics ^b	•						
Pulsed Current ^a	I _{SM}			-	-	- 230	Α	
Forward Voltage	V _{SD}	I _F =	- 85 A, V _{GS} = 0 V	-	- 0.95	- 1.5	V	

Notes

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

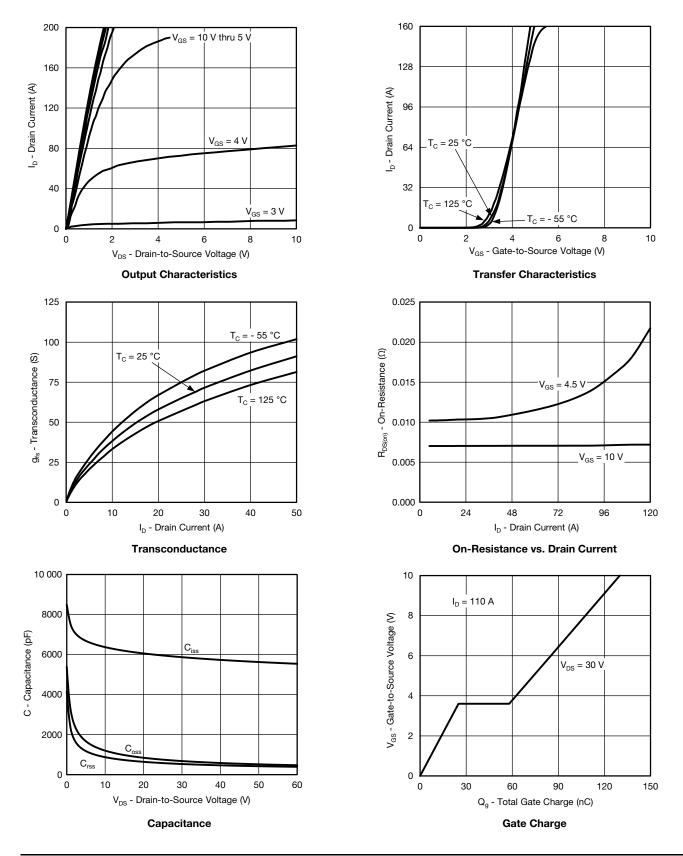
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



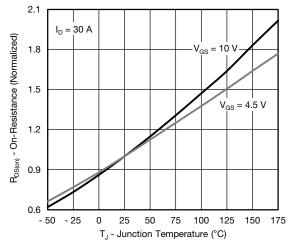
S12-2482-Rev. A, 22-Oct-12

3

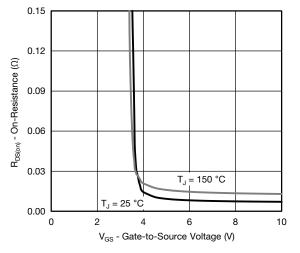
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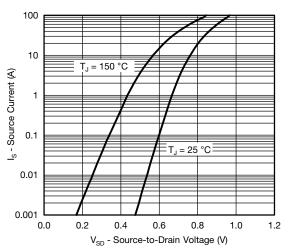
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



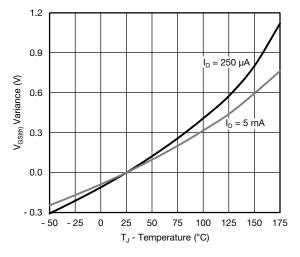
On-Resistance vs. Junction Temperature



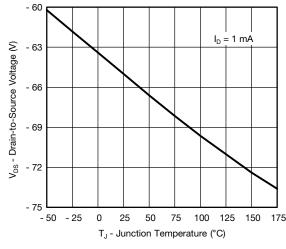
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







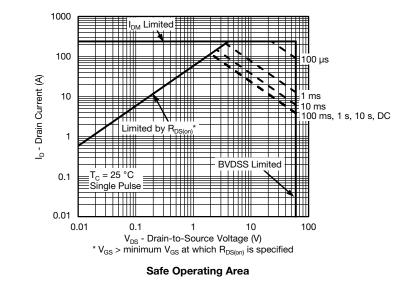
Drain Source Breakdown vs. Junction Temperature

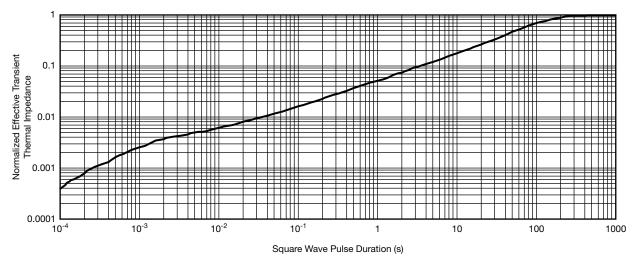
Document Number: 62784

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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

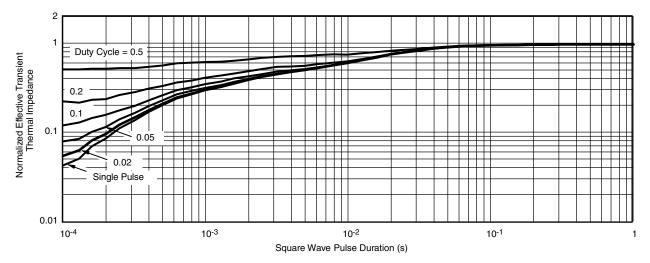




Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

· The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction to Case (25 °C)

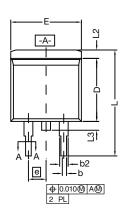
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

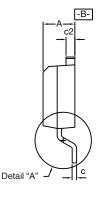
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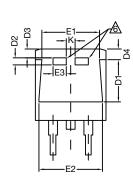


TO-263 (D²PAK): 3-LEAD

VERSION 1: FACILITY CODE = T

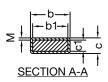








DETAIL A (ROTATED 90°)



		INCHES		MILLIN	IETERS
DIM.		MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
с*	Thin lead	0.013	0.018	0.330	0.457
C	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	E	0.380	0.410	9.652	10.414
	E1	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
е		0.100 BSC		2.54 BSC	
К		K 0.045		1.143	1.397
L		0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
L2		0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
	М	-	0.002	-	0.050

Notes

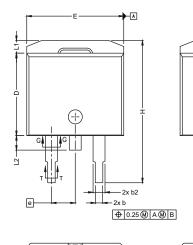
- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB.
- Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

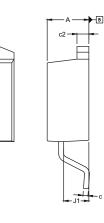
This feature is for thick lead.

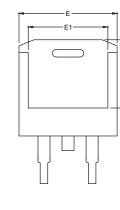
Revison: 28-Oct-2024

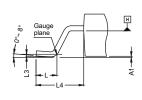


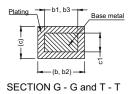
VERSION 2: FACILITY CODE = N











OPTION 1 2 leads



2

 \oplus

3 leads

DIM.	MIN.	MAX.	
A	4.36	4.56	
A1	0	0.25	
b	0.70	0.90	
b1	0.51	0.89	
b2	1.20	1.46	
b3	1.17	1.37	
с	0.38	0.694	
c1	0.38	0.534	
c2	1.19	1.34	
D	8.60	9.00	
D1	6.9	7.5	
E	10.15	10.55	
E1	8.1	8.7	
e	2.54 BSC		
Н	15.0	15.6	
L	1.9	2.5	
L1	-	1.65	
L2	-	1.78	
L3	0.25 typ.		
L4	4.78	5.28	
J1	2.56 2.96		
ECN: S24-1080-Rev. L, 28-Oct-2024 DWG: 5843			



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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